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FDC3601N

Dual N-Channel 100V Specified PowerTrench®MOSFET

General Description

These N-Channel 100V specified MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize on-state resistance and yet maintain low gate charge for superior switching performance.

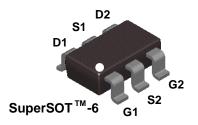
These devices have been designed to offer exceptional power dissipation in a very small footprint for applications where the bigger more expensive SO-8 and TSSOP-8 packages are impractical.

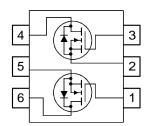
Applications

- Load switch
- · Battery protection
- Power management

Features

- 1.0 A, 100 V. $R_{DS(ON)}$ = 500 m Ω @ V_{GS} = 10 V $R_{DS(ON)}$ = 550 m Ω @ V_{GS} = 6.0 V
- Low gate charge (3.7nC typical)
- Fast switching speed.
- High performance trench technology for extremely low R DS(ON).
- SuperSOTTM-6 package: small footprint 72% (smaller than standard SO-8); low profile (1mm thick).





Absolute Maximum Ratings T_{A=25°C} unless otherwise noted

| Symbol | Parameter | | Ratings | Units |
|-----------------------------------|---|------------|-------------|-------|
| V_{DSS} | Drain-Source Voltage | | 100 | V |
| V _{GSS} | Gate-Source Voltage | | ±20 | V |
| I _D | Drain Current - Continuous | (Note 1a) | 1.0 | А |
| | - Pulsed | | 4.0 | |
| P _D | Power Dissipation for Single Operation | (Note 1a) | 0.96 | W |
| | | (Note 1b) | 0.9 | |
| | | (Note 1c) | 0.7 | |
| T _J , T _{STG} | Operating and Storage Junction Temperat | ture Range | -55 to +150 | °C |

Thermal Characteristics

| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1a) | 130 | °C/W |
|-----------------|---|-----------|-----|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case | (Note 1) | 60 | °C/W |

Package Marking and Ordering Information

| Device Marking | Device | Reel Size | Tape width | Quantity |
|----------------|----------|-----------|------------|------------|
| .601 | FDC3601N | 7" | 8mm | 3000 units |

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|---|---|---|-----|-------------------|-------------------|-------|
| Off Char | acteristics | | l | l | l | l |
| BV _{DSS} | Drain-Source Breakdown Voltage | $V_{GS} = 0 \text{ V}, \qquad I_{D} = 250 \mu\text{A}$ | 100 | | | V |
| <u>ΔBV_{DSS}</u> ΔT _J | Breakdown Voltage Temperature Coefficient | $I_D = 250 \mu\text{A}, \text{Referenced to } 25^{\circ}\text{C}$ | | 105 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 80 \text{ V}, \qquad V_{GS} = 0 \text{ V}$ | | | 10 | μΑ |
| I _{GSSF} | Gate-Body Leakage, Forward | $V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$ | | | 100 | nA |
| I _{GSSR} | Gate-Body Leakage, Reverse | $V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$ | | | -100 | nA |
| On Char | acteristics (Note 2) | · | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$ | 2 | 2.6 | 4 | V |
| $\Delta V_{GS(th)} \over \Delta T_J$ | Gate Threshold Voltage Temperature Coefficient | I_D = 250 μ A,Referenced to 25°C | | - 5 | | mV/°C |
| R _{DS(on)} | Static Drain–Source On–Resistance | $ \begin{array}{cccccccccccccccccccccccccccccccccccc$ | | 370 396 685 | 500 550 976 | mΩ |
| I _{D(on)} | On-State Drain Current | $V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$ | 3 | | | Α |
| g _{FS} | Forward Transconductance | $V_{DS} = 5V$, $I_{D} = 1.0 A$ | | 3.6 | | S |
| Dynamic | Characteristics | | | | | |
| C _{iss} | Input Capacitance | $V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V},$ | | 153 | | pF |
| Coss | Output Capacitance | f = 1.0 MHz | | 5 | | pF |
| C _{rss} | Reverse Transfer Capacitance | | | 1 | | pF |
| Switchin | ng Characteristics (Note 2) | · | | | | |
| t _{d(on)} | Turn-On Delay Time | $V_{DD} = 50 \text{ V}, \qquad I_{D} = 1 \text{ A},$ | | 8 | 16 | ns |
| t _r | Turn-On Rise Time | $V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$ | | 4 | 8 | ns |
| t _{d(off)} | Turn-Off Delay Time | 7 | | 11 | 20 | ns |
| t _f | Turn-Off Fall Time | 7 | | 6 | 12 | ns |
| Q_g | Total Gate Charge | $V_{DS} = 50 \text{ V}, \qquad I_{D} = 1.0 \text{ A},$ | | 3.7 | 5 | nC |
| Q _{gs} | Gate-Source Charge | V _{GS} = 10 V | | 0.8 | | nC |
| Q _{gd} | Gate-Drain Charge | 7 | | 1 | | nC |
| Drain-S | ource Diode Characteristics | and Maximum Ratings | | | | |
| Is | Maximum Continuous Drain-Source | Ţ | | | 0.8 | Α |
| V _{SD} | Drain–Source Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_S = 0.8 \text{ A} \text{(Note 2)}$ | | 0.8 | 1.2 | V |

Notes:

^{1.} $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a) 130 °C/W when mounted on a 0.125 in² pad of 2 oz. copper.



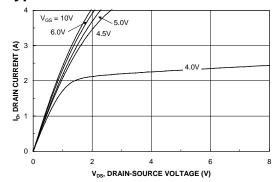
b) 140°C/W when mounted on a .004 in² pad of 2 oz copper



c) 180°C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics



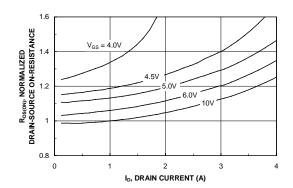
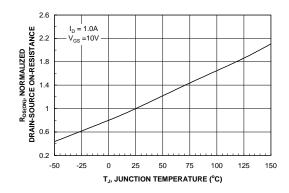


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



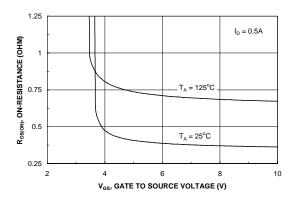
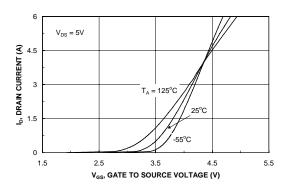


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



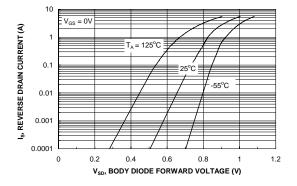
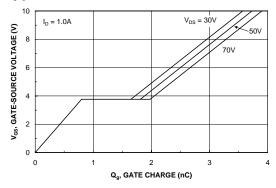


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



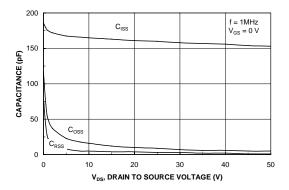
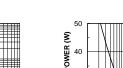
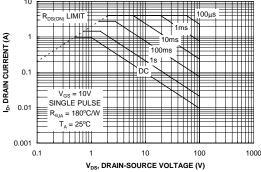


Figure 7. Gate Charge Characteristics.





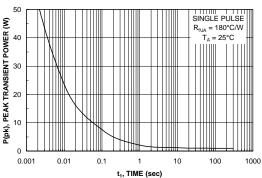


Figure 8. Capacitance Characteristics.

Figure 9. Maximum Safe Operating Area.



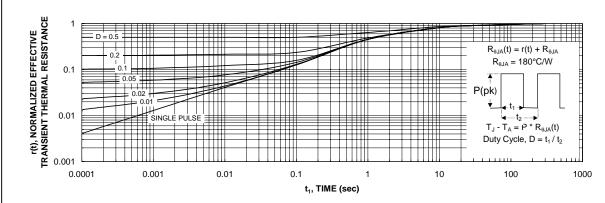


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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